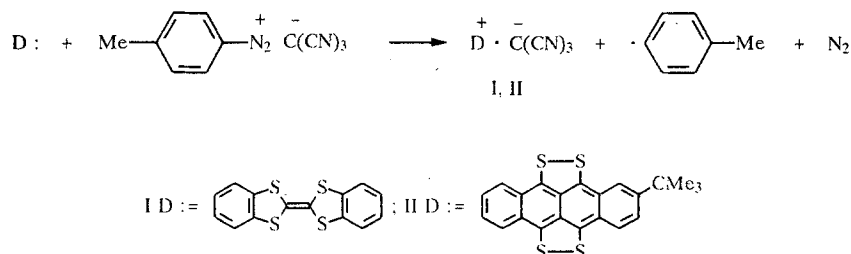


TRICYANOMETHANIDES OF CATION-RADICAL SALTS OF DERIVATIVES OF TETRATHIAFULVALENE AND TETRATHIOTETRACENE

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In the preparation of new organic metals and superconductors among the cation-radical salts of tetrathiafulvalene derivatives the method of electrocrystallization has been largely used [1, 2]. We have shown previously [3] that arenediazonium salts can be used with advantage as one-electron oxidants in the preparation of cation-radical salts of strong electron donors. Employing this method, and using 4-methylbenzenediazonium tricyanomethanide as oxidant, we have prepared for the first time, for the examples of dibenzotetrathiafulvalene and 2-(tert-butyl)tetrathiotetracene, the tricyanomethanides of cation-radical salts by a straightforward chemical route



The electron spectra of the salts prepared show characteristic absorption for the corresponding cation-radicals [3].

4-Methylbenzenediazonium tricyanomethanide was prepared by the reaction of 4-methylbenzenediazonium salts and tricyanomethanide; this will be the subject of a separate communication.

A solution of 0.5 mmole 4-methylbenzenediazonium tricyanomethanide in 1 ml acetonitrile was added, dropwise with stirring, to a solution of 0.5 mmole dibenzotetrathiafulvalene in 20 ml dry benzene. The precipitate was filtered off and washed with benzene and ether to give a 52% yield of dibenzotetrathiafulvalene tricyanomethanide (I). IR spectrum (cm^{-1}): $\nu_{\text{C}=\text{N}}$ 2156 (72); 2176 (88). UV spectrum in dichloroethane in the 400-800 nm range [λ_{max} nm (ϵ): 425 (9700); 446 (10172); 514 (inflection); 644 (6941).

The tricyanomethanide of 2-(tert-butyl)tetrathiotetracene (II) was prepared in a similar manner. Yield 61%. IR spectrum (cm^{-1}): $\nu_{\text{C}=\text{N}}$ 2164. UV spectrum in dichloroethane in the 400-800 nm range [λ_{max} nm (ϵ): 469 (9660); 547 (inflection); 586 (14956).

The results of elemental analyses for compounds I and II were in agreement with those calculated.

REFERENCES

1. M. A. Beno, H. H. Wang, L. Soderholm, K. D. Carlson, L. N. Hall, L. Nuner, H. Rummens, B. Anderson, I. A. Schlueter, I. M. Williams, and M.-H. Whangbo, *Inorg. Chem.*, **28**, 150 (1989).
2. E. B. Yagybskii and R. P. Shibaeva, *J. Molec. Electronics*, **5**, 25 (1989).
3. V. R. Kokars, V. É. Kampar, and O. Ya. Neiland, *Zh. Org. Khim.*, **19**, 1224 (1983).